

MMBT3906T SOT-523 Silicon General Purpose Transistor (PNP)

General description

SOT-523 Silicon General Purpose Transistor (PNP)

FEATURES

- · Simplifies Circuit Design
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

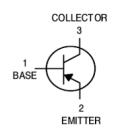
Symbol	Parameter	Value	Units
Vсво	Collector-Base Voltage	-40	V
Vceo	Collector-Emitter Voltage	-40	V
V EBO	Emitter-Base Voltage	-5	V
Ic	Collector Current	-200	mA
P _D	Power Dissipation (FR-4 Board – minimum pad)	200	mW
Reja	Thermal Resistance from Junction to Ambient	600	°C /W
Тл Тэтс	Junction & Storage Temperature Range	-55 to +150	ů

Green Product



SOT-523 (SC-75A)

Electrical Symbol:



Device Marking:

Device Type	Marking
ММВТЗ906Т	2A or 3N

Off Characteristics

Symbol	D	Took Condition	Limits		Unit
	Parameter	Parameter Test Condition	Min	Max	
V(BR)CEO	Collector-Emitter Breakdown Voltage (Note 1)	I _C =-1mA, I _B =0A	-40	-	Volts
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C =-10uA, I _E =0A	-40	-	Volts
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E =-10uA, I _B =0A	-5	-	Volts
Івь	Base Cutoff Current	V _{CE} =-30V, V _{EB} =-3V	-	-50	nA
Icex	Collector Cutoff Current	V _{CE} =-30V, V _{EB} =-3V	-	-50	nA

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%

MMBT3906T



On Characteristics

Symbol	Parameter	Test Condition	Limits		Unit	
			Min	Max		
		Ic =-0.1mA, V _{CE} =-1V	60	-		
		I _C =-1.0mA, V _{CE} =-1V	80	-		
H _{FE}	DC Current Dain	I _C =-10mA, V _{CE} =-1V	100	300	-	
		I _C =-50mA, V _{CE} =-1V	60	-		
		I _C =-100mA, V _{CE} =-1V	30	-		
VCE(sat)	Collector-Emitter Saturation Voltage	I _C =-10mA, I _B =-1mA	-	0.25		
		I _C =-50mA, I _B =-5mA	-	0.4	Volts	
V BE(sat)	Base-Emitter Saturation Voltage	Ic=-10mA, I _B =-1mA	0.65	0.85		
		I _C =-50mA, I _B =-5mA	-	0.95	Volts	

Small-signal Characteristics

Symbol	Parameter	Test Condition	Limits		- Unit	
Зуппоп	Farameter	rest Condition	Min	Max	Oilit	
f⊤	Current-Gain-Bandwidth Product	I _C =-10mA, V _{CE} =-20V, f = 100MHz	250	-	MHz	
Cobo	Output Capacitance	$V_{CB} = -5V$, $I_E = 0A$, $f = 1.0MHz$	-	4.5	pF	
C _{ibo}	Input Capacitance	V _{BE} =-0.5V, I _C =0A, f = 1.0MHz	-	10	pF	
h _{ie}	Input Impedancen	V _{CE} =-10V, I _C =-1mA, f = 1.0kHz	2	12	pF	
h _{re}	Voltage Feedback Ratio	V _{CE} =-10V, I _C =-1mA, f = 1.0kHz	0.1	10	X10 ⁻⁴	
h _{fe}	Small-signal Current Gain	V _{CE} =-10V, I _C =-1mA, f = 1.0kHz	100	400	-	
hoe	Output Admittance	V _{CE} =-10V, I _C =-1mA, f = 1.0kHz	3	60	θ mhos	
NF	Noise Figure	V _{CE} =-5V, I _C =-100uA	4		dB	
	Noise i igure	Rs=1.0k Ω f = 1.0kHz		4	uБ	

Switching Characteristics

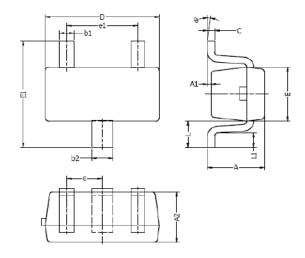
Complete	Parameter	Toot Condition	Limits		11:4
Symbol		Test Condition	Min	Max	Unit
t d	Delay Time	V _{CC} =-3V, V _{BE} =-0.5V,	-	35	nS
t r	Rise Time	I _C =-10mA, I _{B1} =-1mA	-	35	110
t s	Storage Time	V _{CC} =-3V, I _C =-10mA,	-	225	nS
t f	Fall Time	I _{B1} = I _{B2} =-1mA	-	75	113

MMBT3906T



INCHES

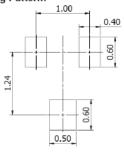
SOT-523 PACKAGE OUTLINE



DIM					
DIW	MIN	MAX	MIN	MAX	
Α	0.70	0.90	0.028	0.035	
A1	0.00	0.10	0.000	0.004	
A2	0.70	0.80	0.028	0.031	
b1	0.15	0.25	0.006	0.010	
b2	0.25	0.35	0.010	0.014	
С	0.10	0.20	0.004	0.008	
D	1.50	1.70	0.059	0.067	
E	0.70	0.90	0.028	0.035	
E1	1.45	1.75	0.057	0.069	
е	0.50 TYP.		0.020 TYP.		
e1	0.90	1.10	0.035	0.043	
L	0.40 REF.		0.016	REF.	
L1	0.10	0.30	0.004	0.012	
θ	0 °	8°	0 °	8°	
IOTES:					

MILLIMETERS

Typical Soldering Pattern:



- NOTES:
 1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
 2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.



Important Notice and Disclaimer

DOESHARE has used reasonable care in preparing the information included in this document, but DOESHARE does not warrant that such information is error free. DOESHARE assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.

DOESHARE no warranty, representation or guarantee regarding the documents, circuits and products specification, DOESHARE reservation rights to make changes for any documents, products, circuits and specifications at any time without notice.

Purchasers are solely responsible for the choice, selection and use of the DOESHARE products and services described herein, and DOESHARE assumes no liability whatsoever relating to the choice, selection or use of the products and services described herein.

No license, express or implied, by implication or otherwise under any intellectual property rights of DOESHARE.

Resale of DOESHARE products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by DOESHARE for the DOESHARE product or service described herein and shall not create or extend in any manner whatsoever, any liability of DOESHARE.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Doeshare manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MMBT-2369-TR BC546/116 BC557/116 BSW67A NJVMJD148T4G NTE123AP-10 NTE153MCP NTE16

NTE195A NTE92 C4460 2N4401-A 2N6728 2SA1419T-TD-H 2SA2126-E 2SB1204S-TL-E 2SC2712S-GR,LF 2SC5488A-TL-H

2SD2150T100R SP000011176 2N2907A 2N3904-NS 2N5769 2SC2412KT146S 2SD1816S-TL-E CPH6501-TL-E MCH4021-TL-E

MJE340 US6T6TR NJL0281DG 732314D CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E FP204
TL-E NJL0302DG 2N3583 2SA2014-TD-E 2SC2812-5-TB-E 30A02MH-TL-E NSV40301MZ4T1G NTE13 NTE26 NTE282 NTE323